

Isc N-Channel MOSFET Transistor

STD10NM60N

• FEATURES

- With To-252(DPAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

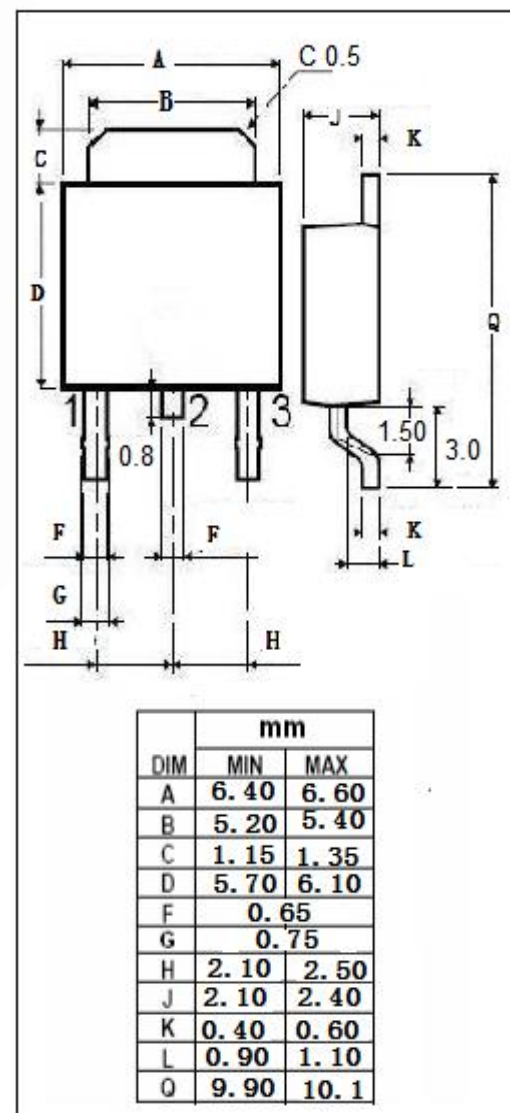
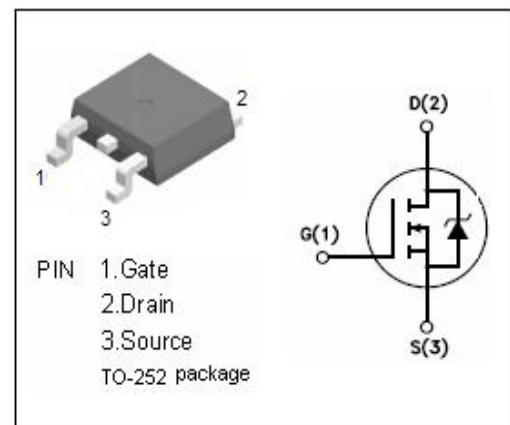
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ ($T_j=175^{\circ}\text{C}$) $T_c=125^{\circ}\text{C}$	10 5	A
I_{DM}	Drain Current-Single Pulsed	32	A
P_D	Total Dissipation @ $T_c=25^{\circ}\text{C}$	70	W
T_{ch}	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	1.79	$^{\circ}\text{C/W}$
$R_{th(ch-b)}$	Thermal resistance junction-pcb max	50	$^{\circ}\text{C/W}$





INCHANGE Semiconductor

Isc N-Channel MOSFET Transistor**STD10NM60N****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1mA$	600			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}= \pm 25V; I_D=0.25mA$	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=4A$		60	65	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}= \pm 25V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V; V_{GS}=0V; T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$			1 100	μA
V_{SDF}	Diode forward voltage	$I_{SD}=8A, V_{GS}=0V$			1.3	V